

# Corporate Introduction of CRESTEC CORPORATION Expert in E-Beam Nanofabrication

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"Financiación-Internacionalización-Cooperación. Iniciativas y Programas para Empresas Nanotecnológicas"

Madrid. 16 de diciembre 2014





## **Corporate Profile of CRESTEC**

- Trade Name
- Type of Business
- Established
- Issued Capital
- President
- Settlement Term
- Head Office
- Tel
- Fax
- E-Mail
- URL
- Bank
- Office Hour

CRESTEC CORPORATION

**Manufacturer** 

**February 10,1995** 

¥45,000,000.-

Hideyuki Ohyi

September

1-9-2, Owada-machi, Hachioji-shi,

**Tokyo 92-0045, Japan** 

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info@crestec8.co.jp

http://www.crestec8.co.jp

**Sumitomo Mitsui** 

**Banking Corporation** 

The Tama Shinkin Bank

Mon. to Fri, 9:00 to 18:00

### Our main business activities

Core Technology : Electron Beam (EB) Nanolithography Technology

EBL Equipment Division

A) Infrastructure Product: XYZ High Resolution EB Lithography System (CABL)

: Unique Features of MODEL CABL-UH Series (130 kV)

B) Development of new product

: Surface Electron Emission Lithography System (CSEL)

Maskless Massively Parallel EB Lithography System (CMPL)

Outsourcing Division

A) Main Service

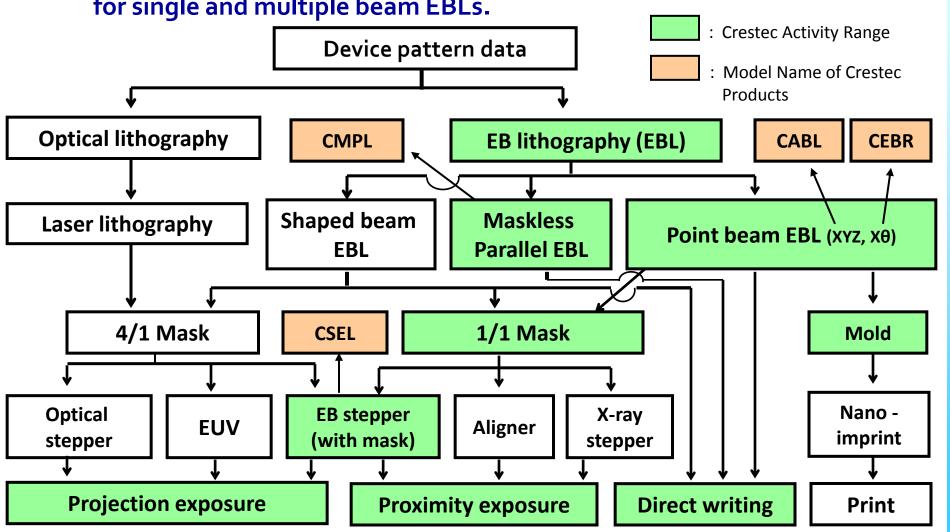
: Foundry Service

(EB exposure and development on Wafers from customer)

: R&D based on customer's demand

### **Outline of Lithography Technology**

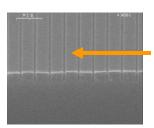
Crestec is producing and developing 2- types of equipment for single and multiple beam EBLs.



# XYZ Type High Resolution EBL System Model CABL-9000C series

CABL-9510C





5.6nm isolated lines

#### **Special features**

- TFE 50kV, 4", 6" or 8" stage
- High resolution better than 10 nm
- High accurate stitch writing for long time by specially designed precise laser interferometer
- Multi-user environment (PC controlled EOC =Recipe )
- Self environment control –Noise reduction from thermal fluctuation, stray magnetic field and floor vibration
- Flexible writing methods (vector, vector R-theta, raster, spot, axial symmetrical, field size modulation, multi-mode, 3D, etc.)
- R&D and production uses
- CE marking

Spot & Defocus

Vector R-theta

Raster

Field size modulation

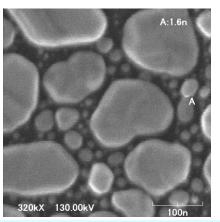
Pitch
200.0nm
200.1nm
200.3nm
200.0nm

#### **ULTRAHIGH RESOLUTION EBL SYSTEM**

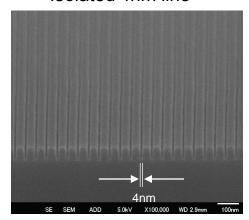
### **Unique Features of MODEL CABL-UH Series**

- Vacc: 130kV Max (25-130kV, 5kV steps)
- Single-Stage Acceleration capability up to 130kV to minimize Electron Gun length for achieving negligible Coulomb blur.
- Micro-Discharge Free Electron Gun.
- Beam Diameter: <1.6nm (1.1nm theoretically)</p>
- Capability of Fine Line: <5nm</p>
- Electrostatic Lens between emitter and anode is designed to achieve very low aberration and shortrange minimized crossover image at the center of blanking electrodes.
- Ultra-stable write capability is achieved using dual thermal controllers.

1.6nm beam size



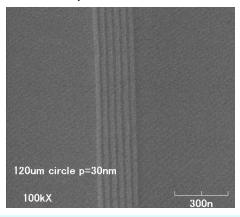
Isolated 4nm line



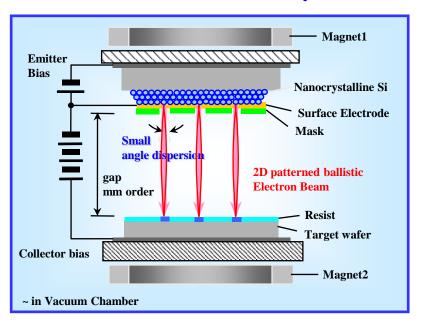
**CABL-UH130 (130kV)** 



hp 15nm L/S



# Surface Electron Emission Lithography System (Model: CSEL series)



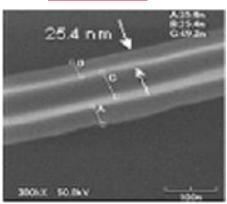
#### **Special features**

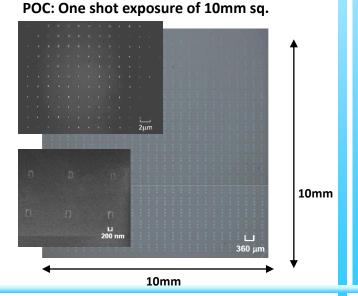
- Massively parallel silicon nanowires give you surface coherent electron emissions which is almost like noncontact nanoimprint to exposure mask patterns by 1 shot.
- Being expected as one of candidate for next generation lithography method.
- Proof of concept has been done beyond 30 nm L&S.
- Si quantum nanowire e-guns (SEED) are Japan-originated technology.
- α tool production for high-bright LED, etc.

**Prototype of CSEL** 

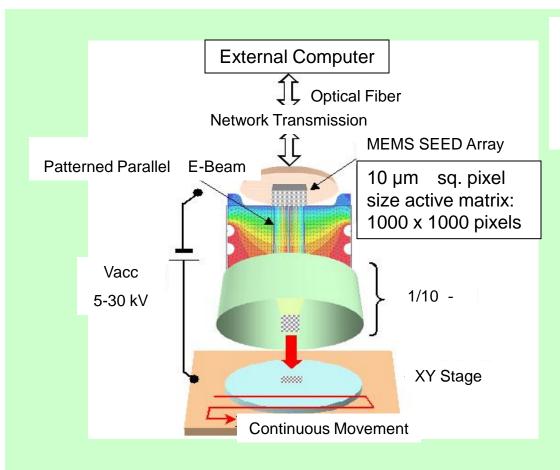


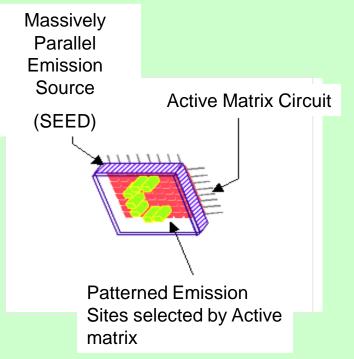
**Sub 30 nm L&S** 





# Maskless Massively Parallel EB Lithography System Model CMPL-6000 (Under Development)





Crestec, Tohoku Univ. and TUAT are jointly developing supported by the Cabinet Office in Japan.

### Funding & Internationalisation

#### **Vision:**

- Distribute high-performance e-beam lithography systems for the production of Nanotechnology to meet and resolve specific needs of our customers:
  - Next generation semiconductors
  - **♦** Plasmonic devices (Sub-5 nm gaps)
  - Quantum effect devices
  - Nano-photonic devices
  - Nano-bio devices
  - Creation of new material patterns without resist
  - Integrated MEMS/NEMS
  - Next generation storage devices
  - **♦** Advanced nano-devices and structures

#### **Targets:**

- Enhance our visibility in the European market.
- Position in the European market through continuous improvement.
- Provide high level support for solving problems in Nanotechnology.

# Funding & Internationalisation

### **Funding needs:**

- Colaboration with ISOM-UPM to share facilities to provide solutions to customers.
- Settlement business in Spain.
- Develop 'EB-Stepper', being expected as one of candidate for next generation lithography method.

# Major Customers over the World (14 Countries and Regions)



### **CRESTEC CORPORATION**

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# Thank you for your attention!

### **Crestec Corporation**

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